

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		200	V
V _{GSS}	Gate-Source Voltage		±25	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S ^a	Diode Continuous Forward Current	T _A =25°C	2.1	A
I _D ^a	Continuous Drain Current	T _A =25°C	2.1	A
		T _A =70°C	1.7	
I _{DM} ^b	Pulsed Drain Current	T _A =25°C	8.4	
P _D ^a	Maximum Power Dissipation	T _A =25°C	3.57	W
		T _A =70°C	2.28	
R _{θJA} ^a	Thermal Resistance-Junction to Ambient	t ≤ 10s	35	°C/W
		Steady State	70	
I _{AS} ^c	Avalanche Current, Single pulse	L=0.5mH	1	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=0.5mH	0.25	mJ

Note a : Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$.

Note b : Pulse width is limited by maximum junction temperature.

Note c : UIS tested and pulse width limited by maximum junction temperature (initial temperature $T_J=25^\circ\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

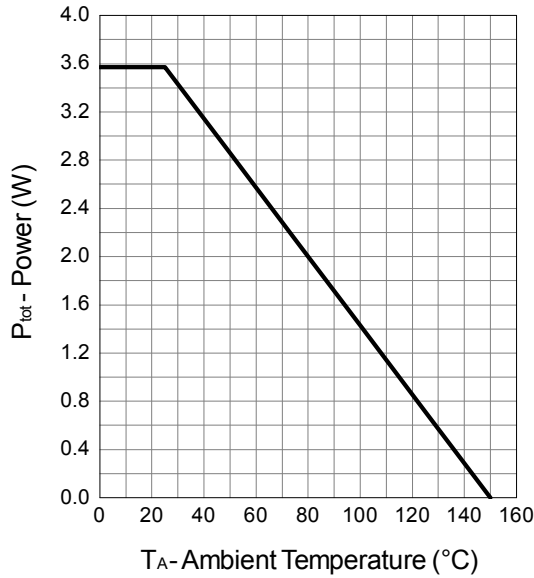
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	200	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =160V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V	-	-	±10	μA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =1.9A	-	320	400	mΩ
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =1.2A, V _{GS} =0V	-	0.8	1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =1.9A, dI _{SD} /dt=100A/μs	-	52	-	ns
Q _{rr}	Reverse Recovery Charge		-	103	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	3	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =100V, Frequency=1.0MHz	-	600	780	pF
C _{oss}	Output Capacitance		-	28	-	
C _{rss}	Reverse Transfer Capacitance		-	13	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	12	22	ns
t _r	Turn-on Rise Time		-	5	9	
t _{d(OFF)}	Turn-off Delay Time		-	19	34	
t _f	Turn-off Fall Time		-	5	9	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =100V, V _{GS} =10V, I _{DS} =1.9A	-	11	16.5	nC
Q _{gs}	Gate-Source Charge		-	3	-	
Q _{gd}	Gate-Drain Charge		-	2.2	-	

Note d : Pulse test ; pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$.

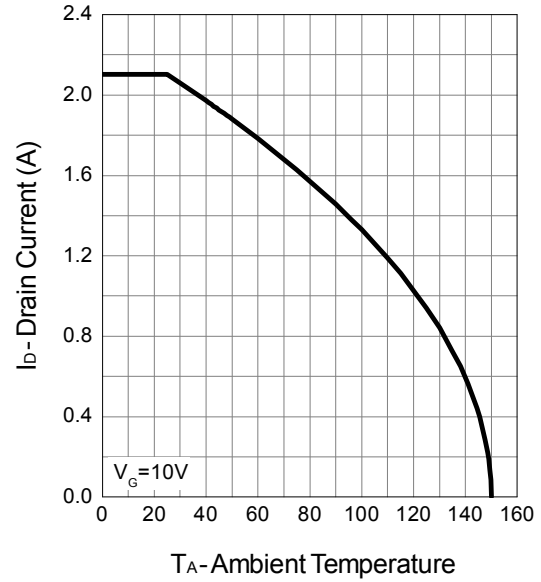
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

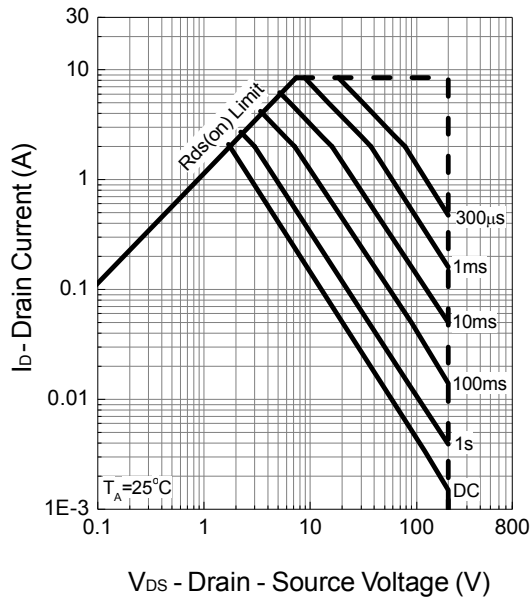
Power Dissipation



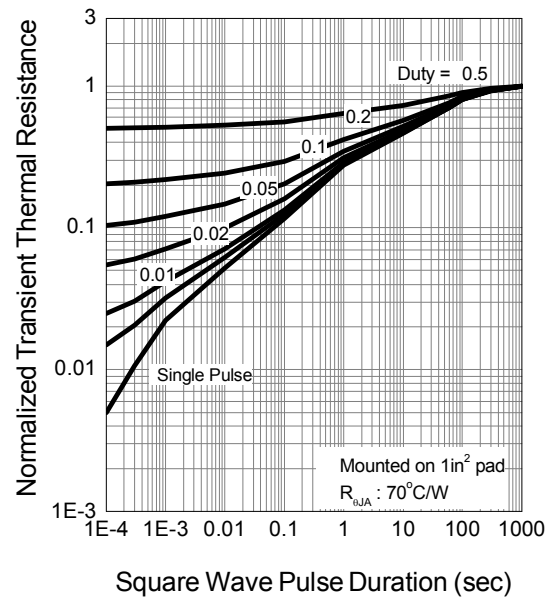
Drain Current



Safe Operation Area

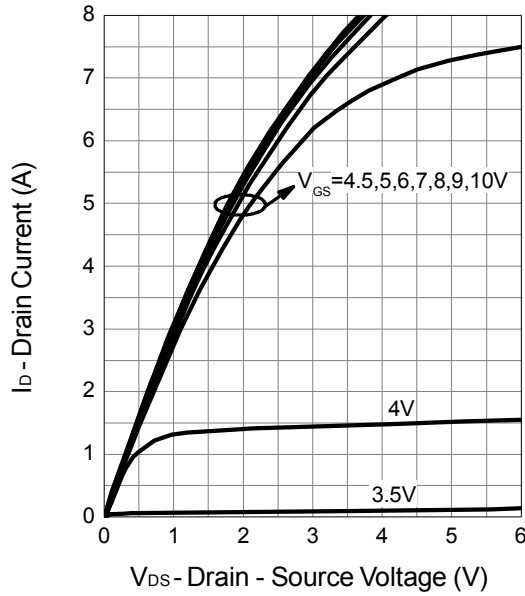


Thermal Transient Impedance

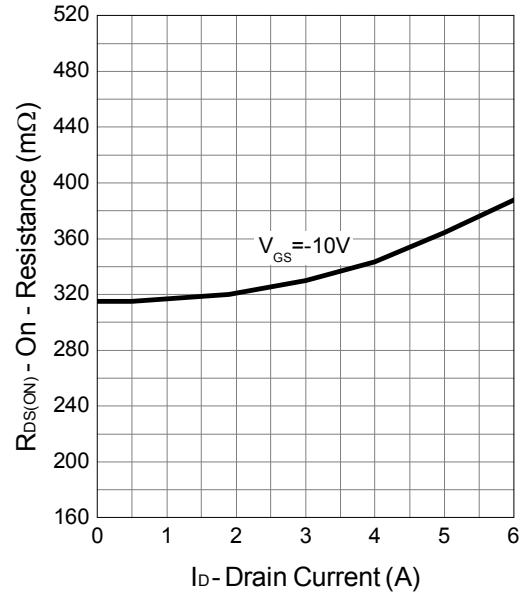


Typical Operating Characteristics (Cont.)

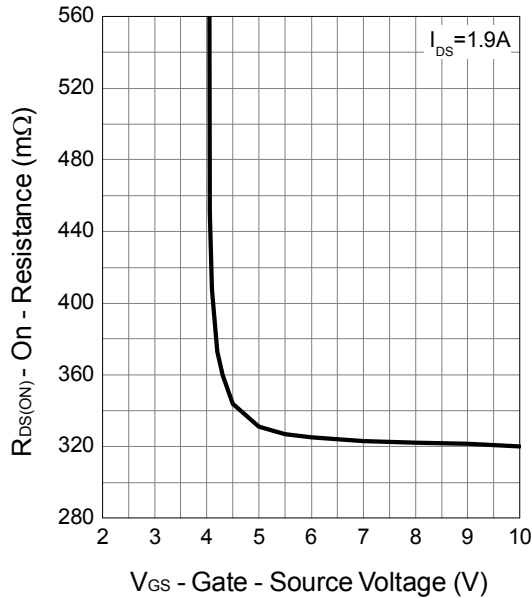
Output Characteristics



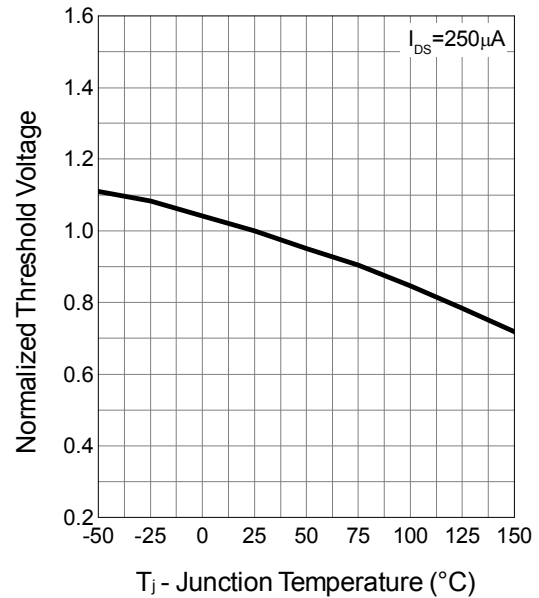
Drain-Source On Resistance



Gate-Source On Resistance

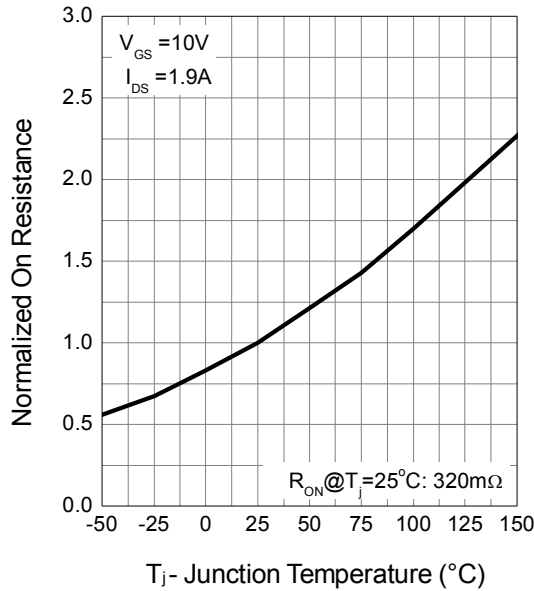


Gate Threshold Voltage

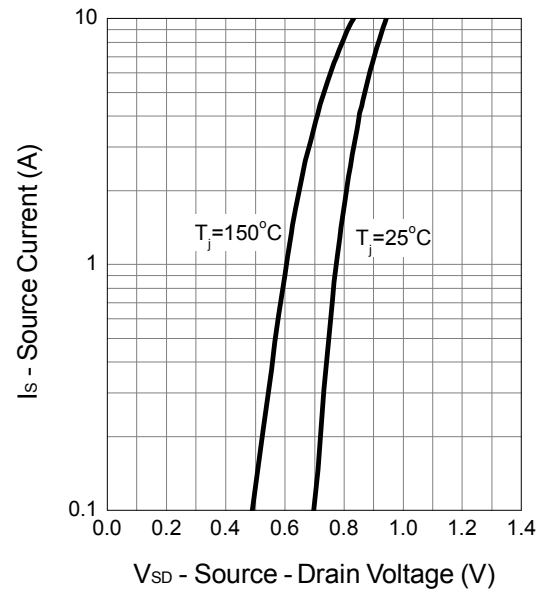


Typical Operating Characteristics (Cont.)

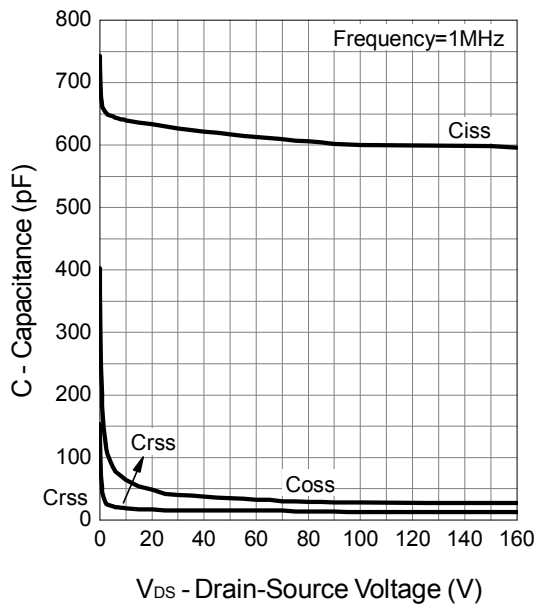
Drain-Source On Resistance



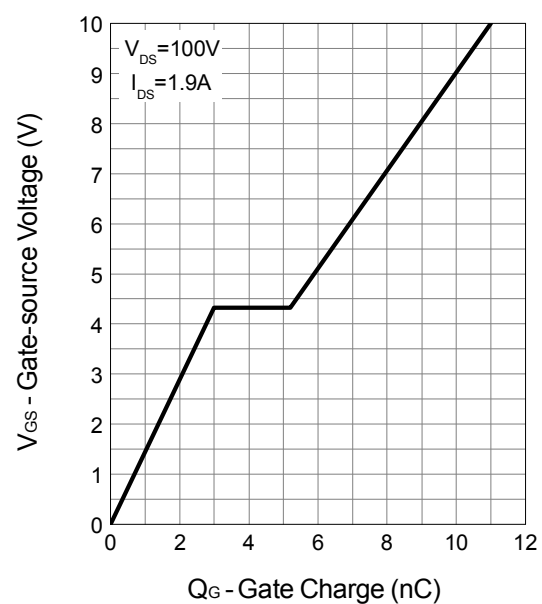
Source-Drain Diode Forward



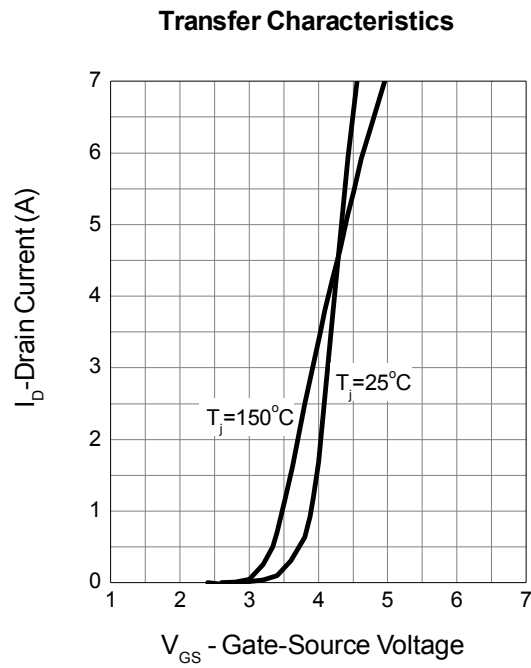
Capacitance



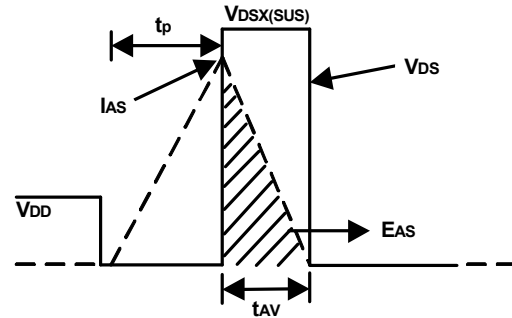
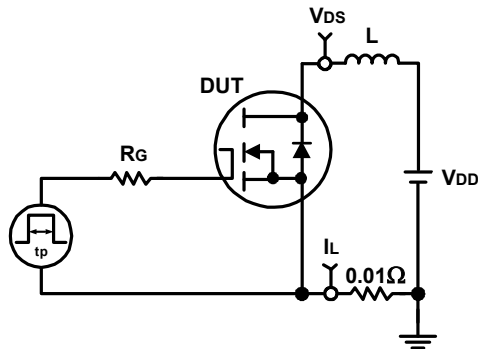
Gate Charge



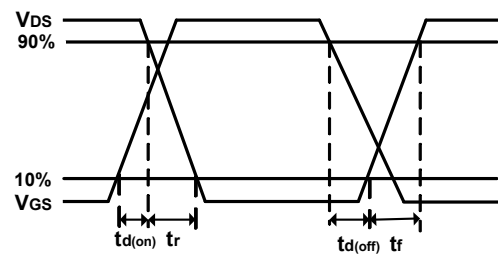
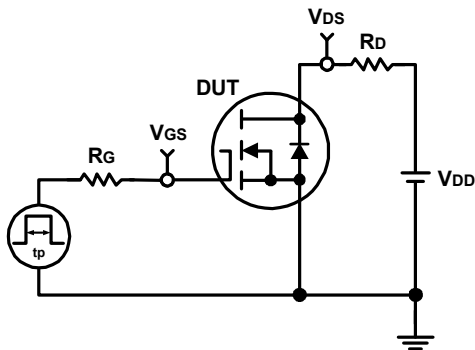
Typical Operating Characteristics (Cont.)



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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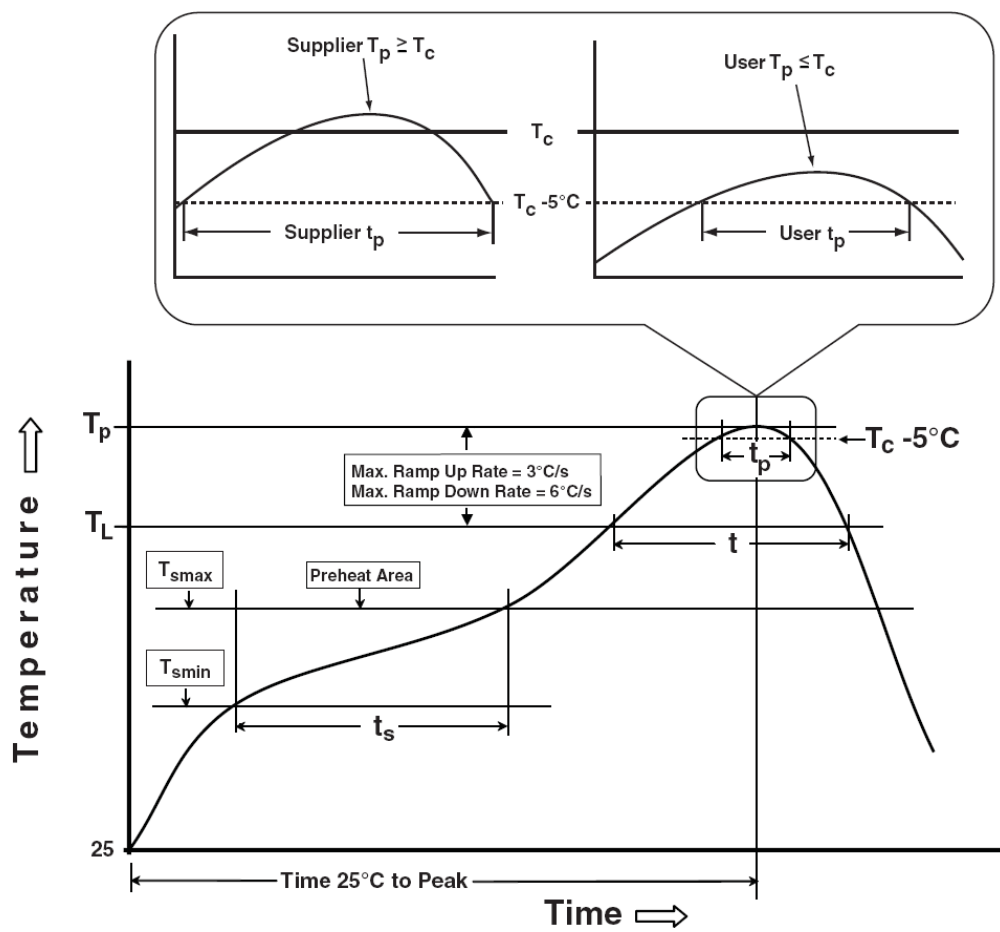
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Customer Service

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